



- ▼ Low On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free

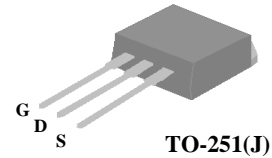
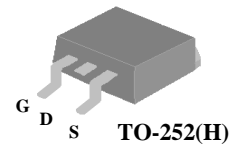


$BV_{DSS}$	40V
$R_{DS(ON)}$	10m $\Omega$
$I_D$	51A

## Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP0904GJ) are available for low-profile applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	+20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	51	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	32	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	200	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	44.6	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	2.8	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>3</sup>	62.5	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^\circ\text{C}/\text{W}$



# AP0904GH/J-HF

## Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	-	10	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	-	15	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	-	45	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =20A	-	9	14.4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =20V	-	2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	6	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =20V	-	6.5	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	6.5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	20	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =20Ω	-	10	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	680	1080	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	160	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	95	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =10A, V <sub>GS</sub> =0V,	-	22	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	16	-	nC

### Notes:

- 1.Pulse width limited by max. junction temperature
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

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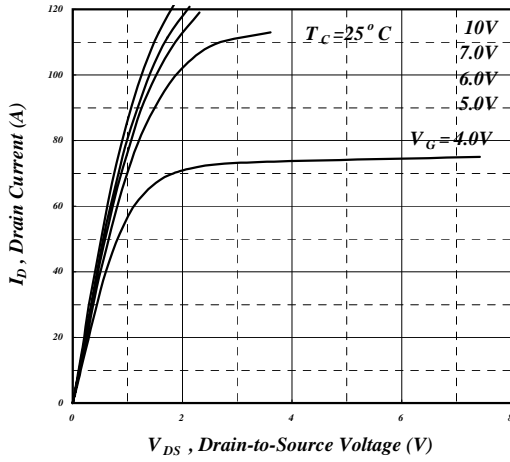


Fig 1. Typical Output Characteristics

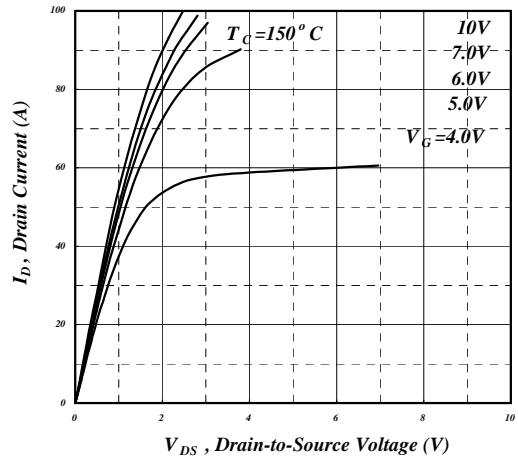


Fig 2. Typical Output Characteristics

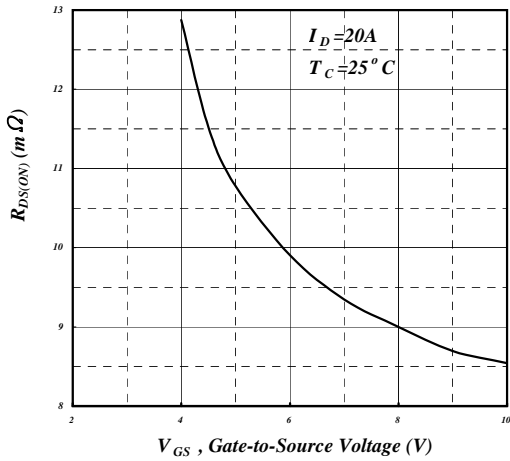


Fig 3. On-Resistance v.s. Gate Voltage

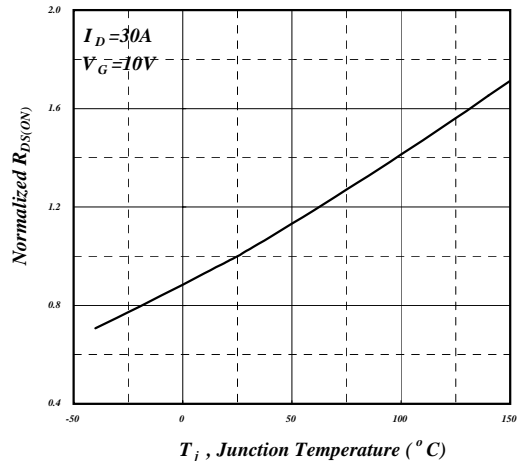


Fig 4. Normalized On-Resistance v.s. Junction Temperature

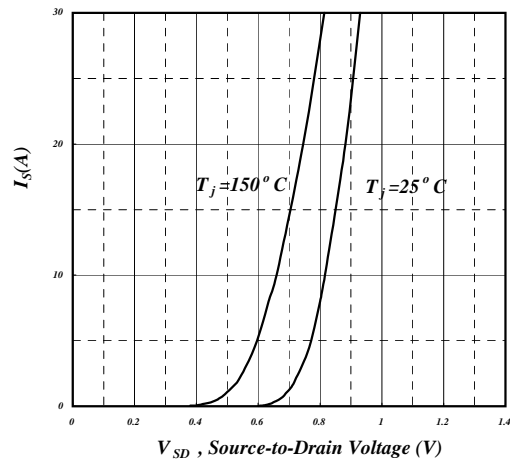


Fig 5. Forward Characteristic of Reverse Diode

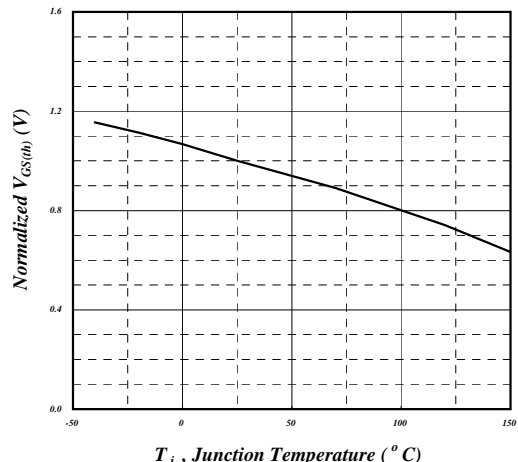


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

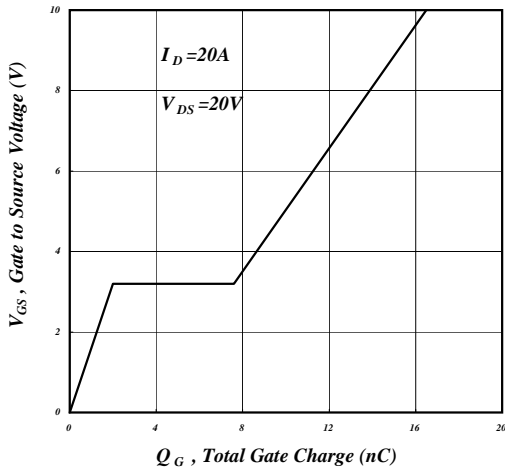


Fig 7. Gate Charge Characteristics

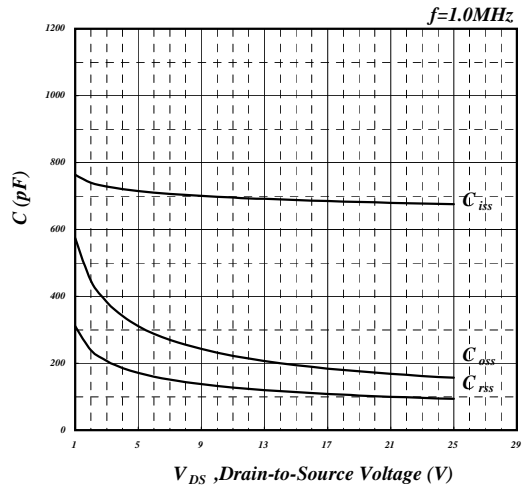


Fig 8. Typical Capacitance Characteristics

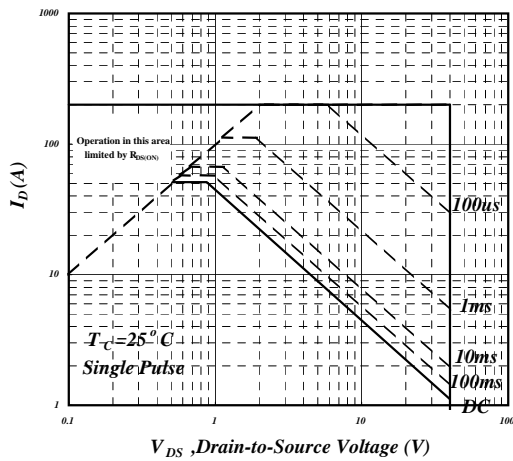


Fig 9. Maximum Safe Operating Area

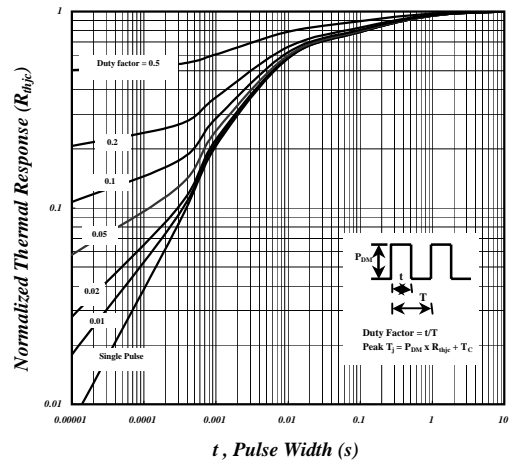


Fig 10. Effective Transient Thermal Impedance



Fig 11. Switching Time Waveform



Fig 12. Gate Charge Waveform